

TLP747JF

GaAs IRED & PHOTO-THYRISTOR

(TLP747JF)

OFFICE MACHINE.
SWITCHING POWER SUPPLY.

The TOSHIBA TLP747JF consists of a photo-thyristor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

All parameters are tested to the specification of TLP747J.
(both condition and limits)

- Peak Off-State Voltage : 600V Min.
- Trigger LED Current : 15mA Max.
- On-State Current : 150mA Max.
- UL Recognized : UL1577, File No.E67349
- BSI Approved : BS415 : 1990, BS7002 : 1989(EN60950)
Certificate No.7364, 7365
- SEMKO Approved : SS4330784
Certificate No.9325163
- Isolation Voltage : 4000Vrms Min.
- Option (D4) type
VDE Approved : DIN VDE0884 / 06.92,
Certificate No. 74286

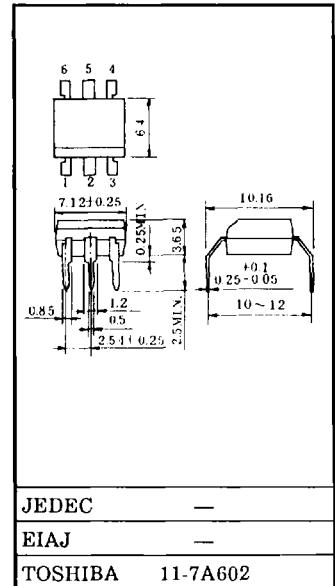
Maximum Operating Insulation Voltage : 890V_{PK}

Highest Permissible Over Voltage : 6000V_{PK}

(Note) When a VDE0884 approved type is needed,
please designate the "Option (D4)"

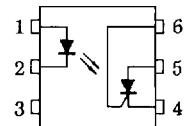
- Creepage Distance : 8.0mm (Min.)
- Clearance : 8.0mm (Min.)
- Internal Creepage Path : 4.0mm (Min.)
- Insulation Thickness : 0.5mm (Min.)
- Conforming Safety Standards :
DIN 57 804.VDE0804 / 1.83
DIN IEC65 / VDE0860 / 8.81
DIN IEC380 / VDE0806 / 8.81
DIN IEC435 / VDE0805 / Draft Nov.84
DIN IEC601T1 / VDE0750T1 / 5.82
BS7002 : 1989 (EN60950)

Unit in mm



Weight : 0.42g

PIN CONFIGURATIONS (TOP VIEW)



- 1 : ANODE
- 2 : CATHODE
- 3 : NC
- 4 : CATHODE
- 5 : ANODE
- 6 : GATE